

Silicon PNP Power Transistors

BDX66C

DESCRIPTION

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- With TO-3 package
- DARLINGTON
- High current

APPLICATIONS

- Designed for power amplification and switching applications.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

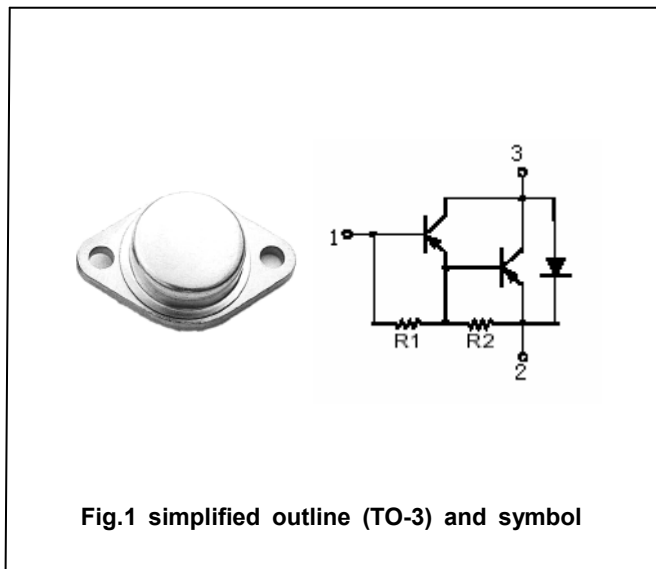


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-120	V
V _{CEO}	Collector-emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-16	A
I _{CM}	Collector current(peak)		-20	A
I _B	Base current		-0.25	A
P _T	Total power dissipation	T _C =25°C	150	W
T _j	Junction temperature		-55~200	°C
T _{stg}	Storage temperature		-55~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.17	°C/W

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=-0.1A$; $I_B=0$; $L=25mH$	-120			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-10A$; $I_B=-40mA$			-2	V
I_{CBO}	Collector cut-off current	$V_{CB}=-70V$; $I_E=0$ $T_C=150^\circ\text{C}$			-1 -5	mA
I_{CEO}	Collector cut-off current	$V_{CE}=-60V$; $I_B=0$			-3	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-5	mA

Switching times

t_{on}	Turn-on time	$I_C=-10A$; $I_{B1}=-I_{B2}=0.04A$ $V_{CC}=12V$;		1.0		μs
t_{off}	Turn-off time			3.5		μs

PACKAGE OUTLINE

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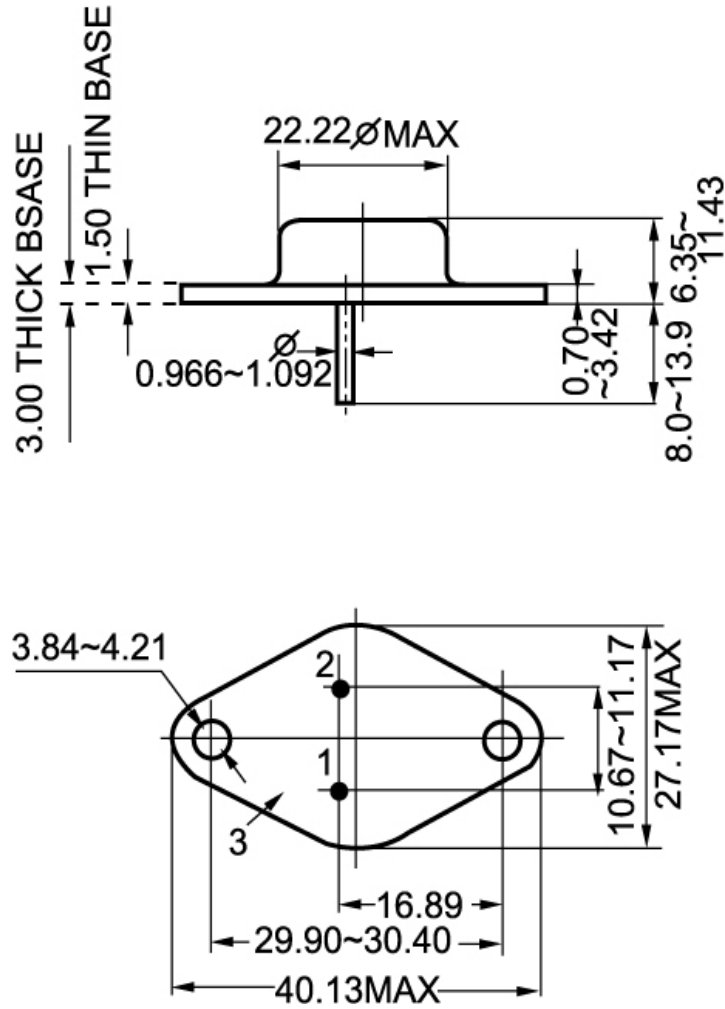


Fig.2 Outline dimensions